Winfried MÃ¶nch

List of Publications by Year
in descending order

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45	2,718	257101	301761
papers	citations	24 h-index	39 g-index

46	46	46	2368
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Valence-band offsets of InGaZnO4, LaAlO3, and SrTiO3 heterostructures explained by interface-induced gap states. Journal of Materials Science: Materials in Electronics, 2018, 29, 19607-19613.	1.1	1
2	Electronic Properties of Semiconductor Interfaces. Springer Handbooks, 2017, , 1-1.	0.3	5
3	Explanation of the barrier heights of graphene Schottky contacts by the MIGS-and-electronegativity concept. Journal of Applied Physics, 2016, 120, 104501.	1.1	13
4	On the band-structure lineup at Ga2O3, Gd2O3, and Ga2O3(Gd2O3) heterostructures and Ga2O3 Schottky contacts. Journal of Materials Science: Materials in Electronics, 2016, 27, 1444-1448.	1.1	13
5	On selenium pâ€“n heterojunctions and Schottky contacts. Journal of Materials Science: Materials in Electronics, 2015, 26, 1097-1101.	1.1	1
6	On the band-structure lineup at Schottky contacts and semiconductor heterostructures. Materials Science in Semiconductor Processing, 2014, 28, 2-12.	1.9	22
7	On the alleviation of Fermi-level pinning by ultrathin insulator layers in Schottky contacts. Journal of Applied Physics, 2012, 111, .	1.1	44
8	Branch-point energies and the band-structure lineup at Schottky contacts and heterostrucures. Journal of Applied Physics, 2011, 109, 113724.	1.1	70
9	Interface-induced gap states and band-structure lineup at TiO2 heterostructures and Schottky contacts. Journal of Applied Physics, 2010, 107, 013706.	1.1	13
10	On the explanation of the barrier heights of InP Schottky contacts by metal-induced gap states. Applied Physics Letters, 2008, 93, .	1.5	22
11	On the electric-dipole contribution to the valence-band offsets in semiconductor-oxide heterostructures. Applied Physics Letters, 2007, 91, .	1.5	44
12	Electronic Properties of Semiconductor Interfaces. , 2006, , 147-160.		1
13	Slope parameters of the barrier heights of metal-organic contacts. Applied Physics Letters, 2006, 88, 112116.	1.5	32
14	Comment on â€œBand gap and band offset of (GaIn)(PSb) lattice matched to InPâ€•[Appl. Phys. Lett. 87, 032102 (2005)]. Applied Physics Letters, 2006, 89, 126101.	1.5	0
15	On the band structure lineup at interfaces of SiO2, Si3N4, and high-Î¹ dielectrics. Applied Physics Letters, 2005, 86, 122101.	1.5	30
16	On the band structure lineup of ZnO heterostructures. Applied Physics Letters, 2005, 86, 162101.	1.5	40
17	Electronic Properties of Semiconductor Interfaces. Springer Series in Surface Sciences, 2004, , .	0.3	179
18	Semiconductor Surfaces and Interfaces. Springer Series in Surface Sciences, 2001, , .	0.3	328

#	Article	IF	Citations
19	Barrier heights of real Schottky contacts explained by metal-induced gap states and lateral inhomogeneities. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1867.	1.6	400
20	Comment on â€œA study on barrier height in Auâ€“AlxGa1â^'xN Schottky diodes in the range 0â‰¤xâ‰¤0.2â€• by M. R. H. Khan, H. Nakayama, T. Detchprohm, K. Hiramatsu and N. Sawaki in Solid-State Electronics, 1997 41, 287. Solid-State Electronics, 1998, 42, 470-471.	0.8	0
21	Valence-band offsets and Schottky barrier heights of layered semiconductors explained by interface-induced gap states. Applied Physics Letters, 1998, 72, 1899-1901.	1.5	73
22	Calculation of valence-band offsets of lattice-matched GaInTlP/InP heterostructures and of Schottky barrier heights of metalâ€“GaInTlP contacts. Applied Physics Letters, 1997, 71, 1231-1233.	1.5	4
23	Oxidation of clean and H-terminated SiC surfaces. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 46, 366-369.	1.7	28
24	Elementary calculation of the branch-point energy in the continuum of interface-induced gap states. Applied Surface Science, 1997, 117-118, 380-387.	3.1	33
25	Barrier heights of GaN Schottky contacts. Applied Surface Science, 1997, 117-118, 388-393.	3.1	67
26	Empirical tightâ€binding calculation of the branchâ€point energy of the continuum of interfaceâ€induced gap states. Journal of Applied Physics, 1996, 80, 5076-5082.	1.1	163
27	Chemical trends of barrier heights in metal-semiconductor contacts: on the theory of the slope parameter. Applied Surface Science, 1996, 92, 367-371.	3.1	103
28	Electronic properties of ideal and interface-modified metal-semiconductor interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2985.	1.6	70
29	Schottky contacts on ternary compound semiconductors: Compositional variations of barrier heights. Applied Physics Letters, 1995, 67, 2209-2211.	1.5	17
30	Semiconductor Surfaces and Interfaces. Springer Series in Surface Sciences, 1995, , .	0.3	282
31	Metal-semiconductor contacts: electronic properties. Surface Science, 1994, 299-300, 928-944.	0.8	202
32	Barrier Heights of 3Câ€“ and 6Hâ€“SiC Schottky Contacts: Explanation by the MIGSâ€“andâ€“Electronegativity Model. , 1994, , 169-174.		4
33	Mechanisms of barrier formation in schottky contacts: Metal-induced surface and interface states. Applied Surface Science, 1990, 41-42, 128-138.	3.1	18
34	Mechanisms of Barrier Formation in Schottky Contacts. NATO ASI Series Series B: Physics, 1989, , 11-38.	0.2	6
35	Chemical trends in Schottky barriers: Charge transfer into adsorbate-induced gap states and defects. Physical Review B, 1988, 37, 7129-7132.	1.1	74
36	Mechanisms of Schottky-barrier formation in metalâ€“semiconductor contacts. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1270.	1.6	111

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37	Deep Levels at Compound-Semiconductor Interfaces. NATO ASI Series Series B: Physics, 1988, , 253-287.	0.2	0
38	On the oxidation of IIIâ€“V compound semiconductors. Surface Science, 1986, 168, 577-593.	0.8	53
39	On the present understanding of Schottky contacts. FestkÃ¶rperprobleme, 1986, , 67-88.	0.7	18
40	Electronic properties and chemical interactions at IIIâ€“V compound semiconductor surfaces: Germanium and oxygen on GaAs(110) and InP(110) cleaved surfaces. Applications of Surface Science, 1985, 22-23, 705-723.	1.0	25
41	On the surface physics of IIIâ€“V compound semiconductors. , 1984, , 229-268.		3
42	Electronic characterization of compound semiconductor surfaces and interfaces. Thin Solid Films, 1983, 104, 285-299.	0.8	28
43	On the correlation of geometrical structure and electronic properties at clean semiconductor surfaces. Surface Science, 1977, 63, 79-95.	0.8	53
44	ï¿½ber die charakteristische Temperatur? R abschreckend kondensierter Metallschichten. European Physical Journal A, 1962, 170, 93-104.	1.0	8
45	Messung der Fehlordnungsenergie an abschreckend kondensiertem Kupfer bei tiefer Temperatur. European Physical Journal A, 1959, 157, 149-158.	1.0	17